

PBSS5130PAP

30 V, 1 A PNP/PNP low VCEsat (BISS) transistor 12 December 2012

Product data sheet

General description 1.

PNP/PNP low V_{CFsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4130PANP. NPN/NPN complement: PBSS4130PAN.

2. **Features and benefits**

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	-30	V
I _C	collector current			-	-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-2	Α
Per transistor	Per transistor						
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -0.1 A; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C		-	-	250	mΩ



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	Transparent top view Sym138 DFN2020-6 (SOT1118)	E1 B1 C2
6	C1	collector TR1		sym138
7	C1	collector TR1	DI 112020-3 (0011110)	
8	C2	collector TR2		

Ordering information

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
PBSS5130PAP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118			

Marking 7.

Marking codes Table 4.

Type number	Marking code
PBSS5130PAP	2E

Limiting values 8.

Table 5. **Limiting values**

PBSS5130PAP

In accordance with the Absolute Maximum Rating System (IEC 60134).

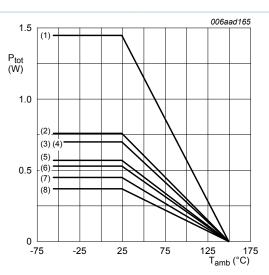
Symbol	Parameter	Conditions		Min	Max	Unit		
Per transistor	Per transistor							
V _{CBO}	collector-base voltage	open emitter		-	-30	V		
V _{CEO}	collector-emitter voltage	open base		-	-30	V		
V _{EBO}	emitter-base voltage	open collector		-	-7	V		
I _C	collector current			-	-1	Α		
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-2	Α		
I _B	base current			-	-0.3	Α		

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Symbol	Parameter	Conditions	l l	Min	Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			[5]	-	450	mW
			[6]	-	760	mW
			[7]	-	700	mW
			[8]	-	1450	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
			[8]	-	2000	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- 6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

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- (1) 4-layer PCB 70 μm, mounting pad for collector 1 cm²
- (2) FR4 PCB 70 µm, mounting pad for collector 1 cm²
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm²
- (5) FR4 PCB 35 μm, mounting pad for collector 1 cm²
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						,
R _{th(j-a)}	thermal resistance	hermal resistance in free air	[1]	-	-	338	K/W
	from junction to ambient		[2]	-	-	219	K/W
ambient		[3]	-	-	236	K/W	
		[4]	-	-	179	K/W	
		[6 [7	[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R _{th(j-a)}	thermal resistance in free air from junction to ambient	[1]	-	-	245	K/W	
		nbient	[2]	-	-	160	K/W
			[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

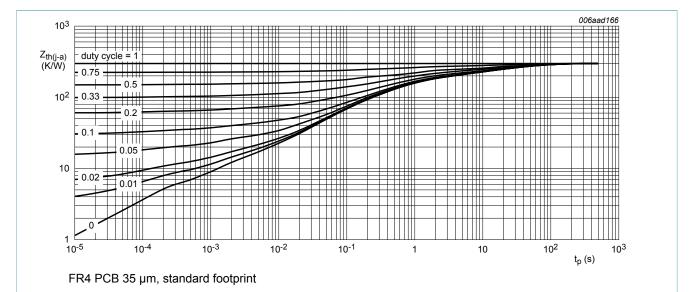


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

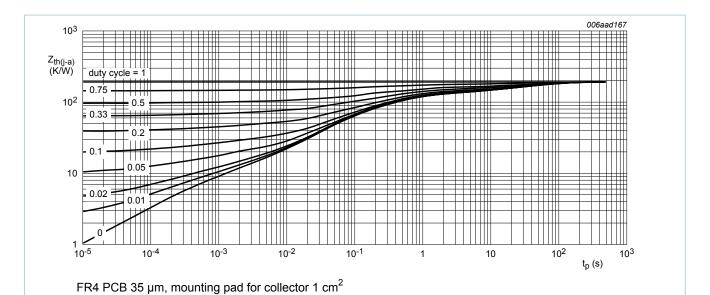


Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

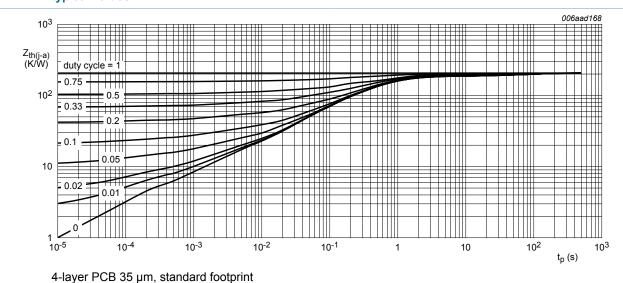


Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

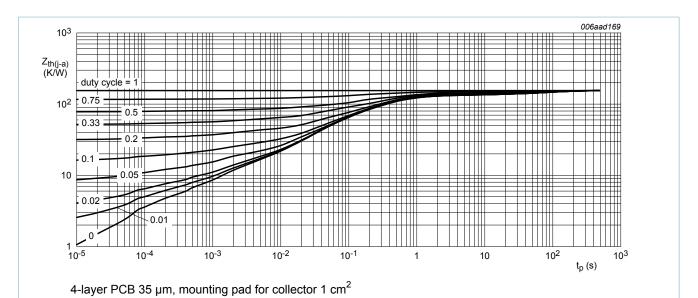


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

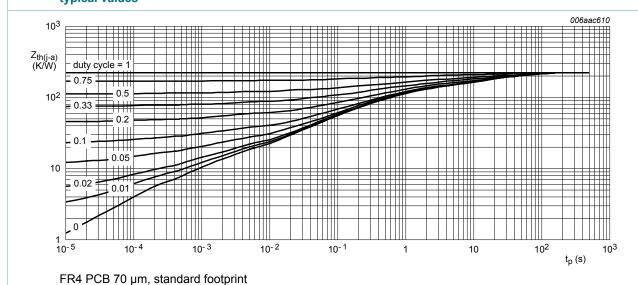


Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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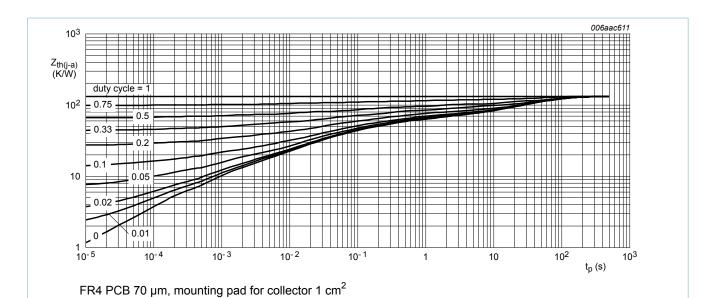
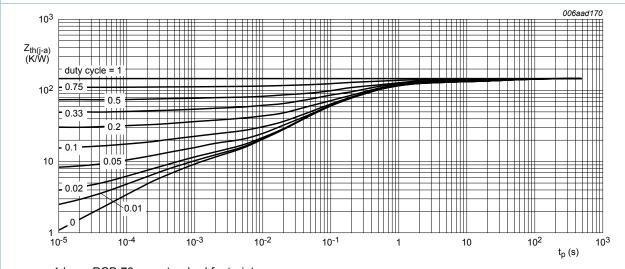


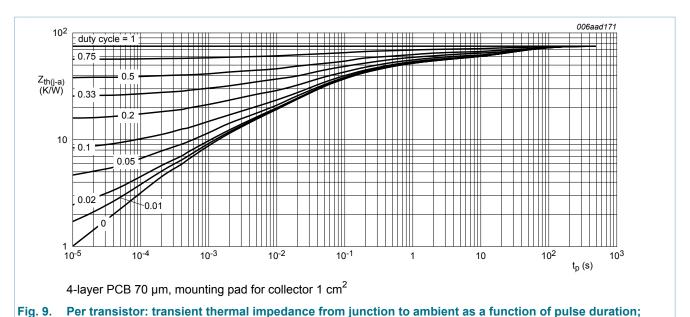
Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 70 μm, standard footprint

Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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typical values

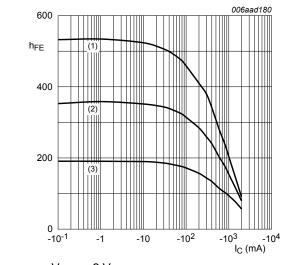
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
I _{CBO}	collector-base cut-off	V _{CB} = -24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -24 V; I_{E} = 0 A; T_{j} = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE} DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	250	350	-		
	V_{CE} = -2 V; I_{C} = -500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	170	250	-		
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb} = 25 \ ^{\circ}C$	120	175	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-85	-140	mV
		I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-175	-280	mV
		I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-160	-250	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -0.1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C$	-	-	250	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat} base-emitter saturation voltage	base-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-1	V
		I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-	-1	V
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-0.9	V
t _d	delay time	V_{CC} = -10 V; I_{C} = -0.5 A; I_{Bon} = -25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = 25 mA; T _{amb} = 25 °C	-	35	-	ns
t _{on}	turn-on time		-	50	-	ns
ts	storage time		-	105	-	ns
t _f	fall time		-	35	-	ns
t _{off}	turn-off time		-	140	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	65	125	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	13	17	pF



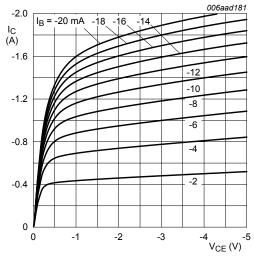
V_{CE} = −2 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

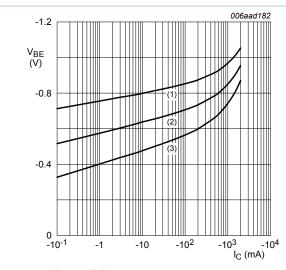
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 11. Collector current as a function of collectoremitter voltage; typical values



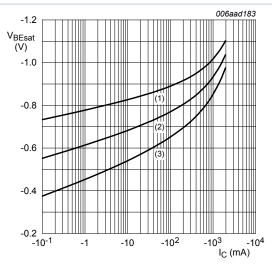
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. Base-emitter voltage as a function of collector current; typical values



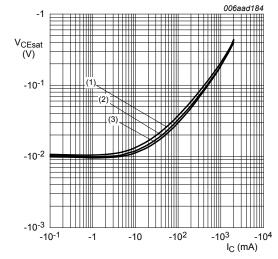
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. Base-emitter saturation voltage as a function of collector current; typical values



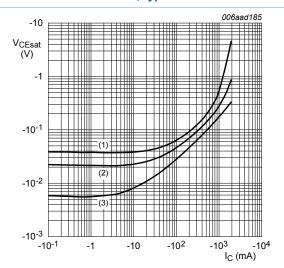
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

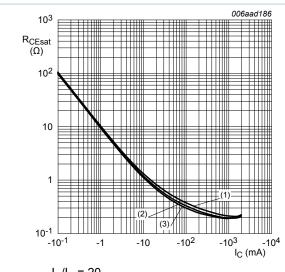


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values



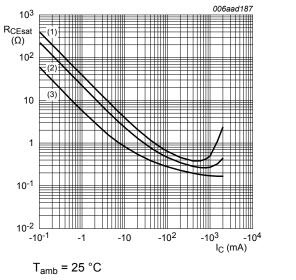
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

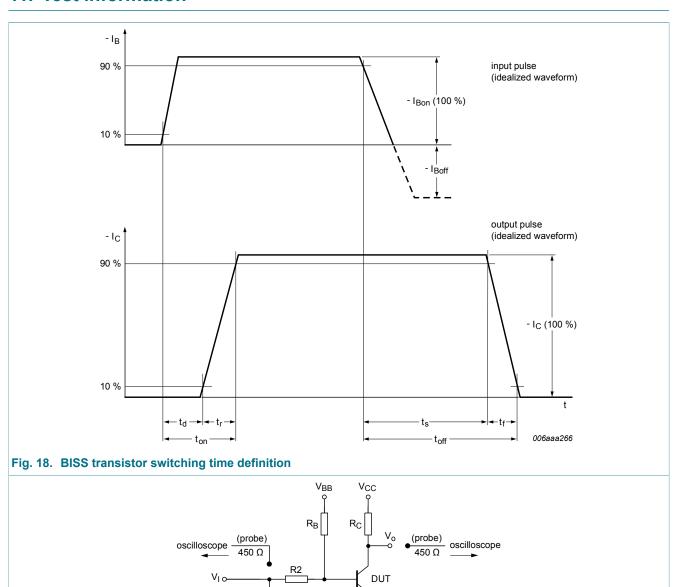


Fig. 19. Test circuit for switching times

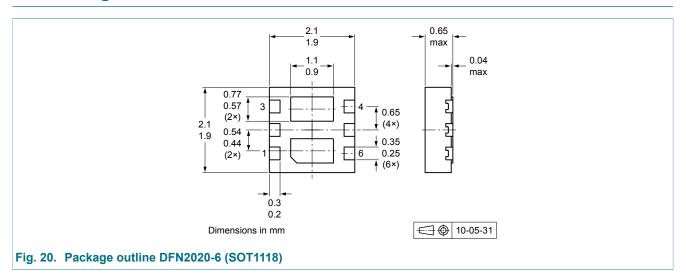
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

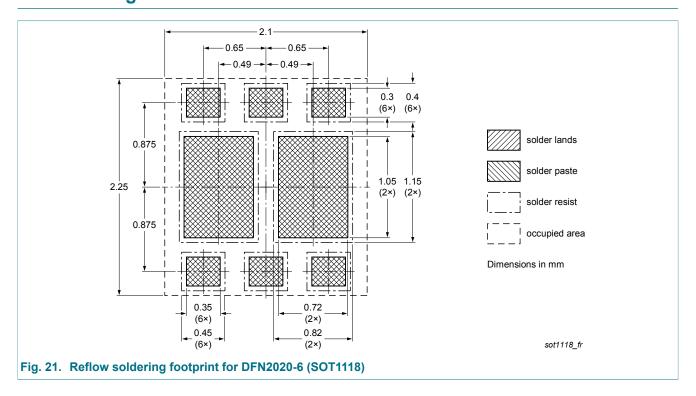
mgd624

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12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5130PAP v.1	20121212	Product data sheet	-	-		

PBSS5130PAP

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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